

Abstract of the Disclosure

A method of selective etching a metal oxide layer for fabrication of a ferroelectric device includes preparing a silicon substrate, including forming an oxide layer thereon; depositing a layer of metal or metal oxide thin film on the substrate; patterning and selectively etching the metal or metal oxide thin film without substantially over etching into the underlying oxide layer; 5 depositing a layer of ferroelectric material; depositing a top electrode on the ferroelectric material; and completing the ferroelectric device.